Time		Coherence	Qubit	Material	Host	Date	Reference	Source
57	s	T_1	LD/e	GaAs/AlGaAs	2D	2018-08	1	p3 and Fig. 4a
43	s	T_1	LD/i	Si:P	imp	2024-03	2	Tab. 2 and Fig. 4
30	s	T_1	LD/i	Si:P	imp	2017-03	3	Fig. 2b the lowest point
30	s[a]	T_1	LD/h	BLG	2D	2025-02	4	p3
16	s	T_1	LD/i	Si:P	imp	2023-11	5	Tab. I
11	s[b]	T_1	LD/i	Si:P	imp	2023-02	6	p6
11	s	T_1	ST/e	Si/SiO_2	2D	2024-03	7	p4
10	s	T_1	LD/e	GaAs/AlGaAs	2D	2017-10	8	Fig. 2 the lowest green point
9.8	s	T_1	LD/i	Si:P	imp	2019-05	9	Fig. 2c
9.3	s	T_1	LD/i	Si:P	imp	2018-03	10	p3 and Fig. 1f
9	s	T_1	LD/e	Si/SiO_2	1D	2021-03	11	p3 and Fig. 3a the leftmost blue point
6.5	s	T_1	LD/i	^{28}Si:P	imp	2023-02	12	Fig. 3c
6	s	T_1	LD/i	Si:P	imp	2010-09	13	p2
5	s[c]	T_1	LD/e	Si/SiGe	2D	2019-04	14	p4
4.2	s	T_1	LD/i	Si:P	imp	2019-01	15	p3
3.4	s	T_1	LD/i	^{28}Si:P	imp	2021-01	16	p6 and SFig. 3c
3	s	T_1	LD/i	^{28}Si:P	imp	2016-10	17	p3
3	s	T_1	ST/e	Si/SiGe	2D	2012-01	18	p4
2.8	s	T_1	LD/e	Si/SiGe	2D	2011-04	19	p3 and Fig. 3
2.6	s	T_1	LD/e	Si/SiO_2	2D	2013-06	20	p3
1.8	s	T_1	LD/i	Si:P	imp	2013-06	21	Fig. 3
1.6	s	T_1	LD/e	$^{28}Si/SiO_2$	2D	2022-03	22	p4 and Fig. 3c
1.3	s	T_1	LD/i[d]	^{28}Si:P	imp	2016-10	23	p4
1.3	s	T_1	LD/i	Si:P	imp	2018-11	24	p3 and Fig. 2b
1	s	T_1	LD/e	^{28}Si/SiGe	2D	2020-03	25	p6 and Fig. 4a
1	s	T_1	LD/e	$^{28}Si/SiO_2$	2D	2018-10	26	p2
1	s	T_1	LD/e	GaAs/AlGaAs	2D	2008-01	27	p4 and Fig. 3c the leftmost blue point
0.7	s	T_1	LD/i	Si:P	imp	2012-09	28	p3
0.6	s[e]	T_1	LD/e	Si/SiGe	2D	2009-08	29	Fig. 5
0.5	s[f]	T_1	ST/e	$^{28}Si/SiO_2$	2D	2020-04	30	Fig. 4 the leftmost black point
0.4	s	T_1	LD/h	BLG	2D	2025-02	4	p4
0.35	s[g]	T_1	HY/e	BLG	2D	2024-01	31	Fig. 3b
0.17	s	T_1	LD/e	Si/SiGe	2D	2016-11	32	Fig. 6
0.16	s[h]	T_1	LD/e	Si/SiGe	2D	2019-04	14	Fig. 2
0.15	s[i]	T_1	LD/e	$^{28}Si/SiO_2$	2D	2018-08	33	p2 and p4
0.14	s	T_1	ST/e	Si/SiGe	2D	2012-04	34	Fig. 2d
0.13	s	T_1	LD/e	^{28}Si/SiGe	2D	2019-11	35	p4
90	ms	T_1	LD/e	Si/SiO_2	2D	2020-06	36	Fig. 1c
85	ms	T_1	LD/e	GaAs/AlGaAs	2D	2014-12	37	p2 and Fig. 3
50	ms	T_1	LD/e	Si/SiGe	2D	2018-02	38	p1 and ED Fig. 3b
40	ms	T_1	LD/e	Si/SiO_2	2D	2010-03	39	p4 and Fig. 4 the leftmost red point
34	ms	T_1	ST/e	BLG	2D	2024-01	31	Fig. 3b
32	ms	T_1	LD/h	Ge/SiGe	2D	2020-08	40	p3
32	ms	T_1	LD/e	^{28}Si/SiGe	2D	2022-12	41	p3
22	ms[j]	T_1	LD/e	Si/SiGe	2D	2022-08	42	p2 and ED Fig. 4b-d
20	ms	T_1	HY/e[k]	^{28}Si/SiGe	2D	2022-03	43	p5
16	ms	T_1	LD/h	Ge/SiGe	2D	2021-03	44	Fig. S5 dot 3
15	ms[l]	T_1	ST/e	$^{28}Si/SiO_2$	2D	2020-04	30	Fig. 4 the rightmost black point
11	ms[m]	T_1	LD/e	$^{28}Si/SiO_2$	2D	2024-03	45	p3
10	ms	T_1	LD/e	Si/SiO_2	1D	2022-03	46	p2 and Fig. 2a

TABLE I-1. Spin coherence times (part 1). Superscripts stand for the following. [a]: Spin-valley relaxation. [b]: Dot D3. [c]: No micromagnet. [d]: Qubit defined in the rotating frame. [e]: *(estimated)* Fig. 5 the lowest point. [f]: At 0.04 K. [g]: Valley degree of freedom. [h]: With micromagnet. [i]: At 0.1 K. [j]: The average over the three qubits. [k]: EO qubit. [l]: At 1.5 K. [m]: At 1 K.

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